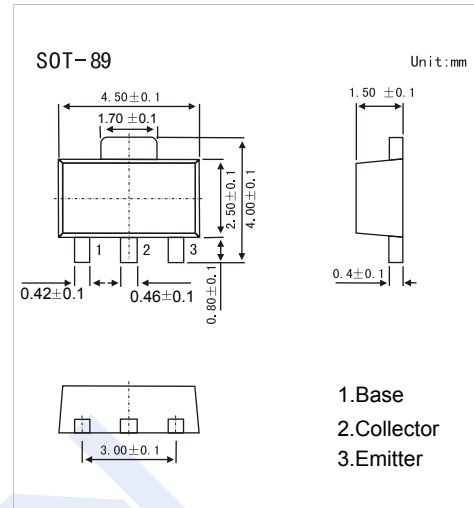


PNP Transistors

2SA1369

■ Features

- High Collector Current ($I_{CM} = -3A$, $I_C = -1.5A$)
- High Collector Dissipation $P_C = 500mW$
- Small Package For Mounting
- Complementary to 2SC3439

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-1.5	A
Peak Collector Current	I_{CM}	-3	A
Collector Power Dissipation	P_C	500	mW
Junction temperature	T_j	+150	$^\circ C$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu A$, $I_E = 0$	-30			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 mA$, $R_{BE} = \infty$	-20			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu A$, $I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -20 V$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1A$, $I_B = -20mA$		-0.25	-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1A$, $I_B = -20mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -6V$, $I_C = -500mA$	400		1200	
Collector Output Capacitance	C_{ob}	$V_{CE} = -10V$, $I_E = 0$, $f = 1MHz$		37		pF
Transition frequency	f_T	$V_{CE} = -10V$, $I_E = 10mA$		90		MHz

■ Classification of h_{FE}

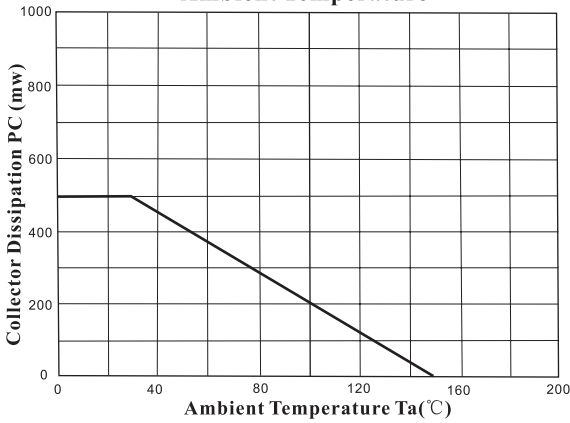
Marking	GG	GH
Rank	G	H
h_{FE}	400 ~ 800	600 ~ 1200

PNP Transistors

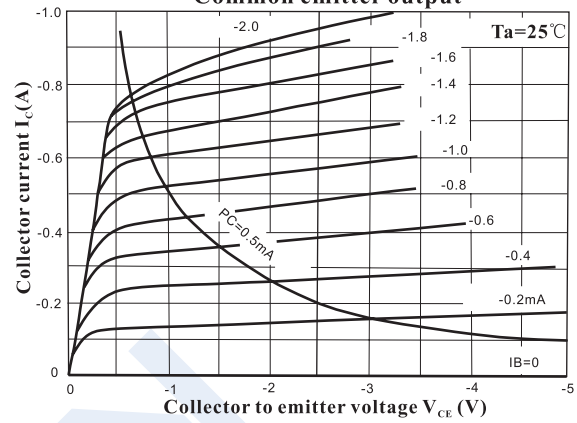
2SA1369

■ Typical Characteristics

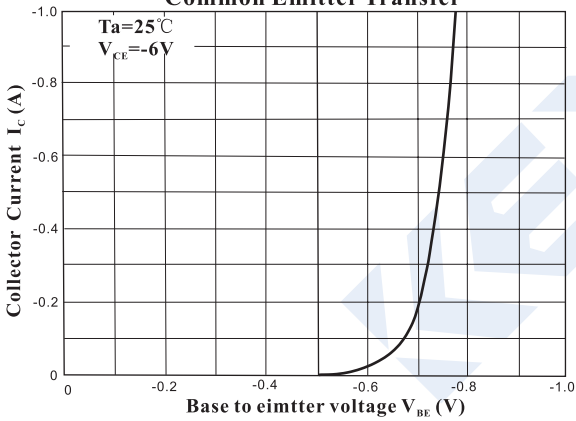
Collector Dissipation vs Ambient Temperature



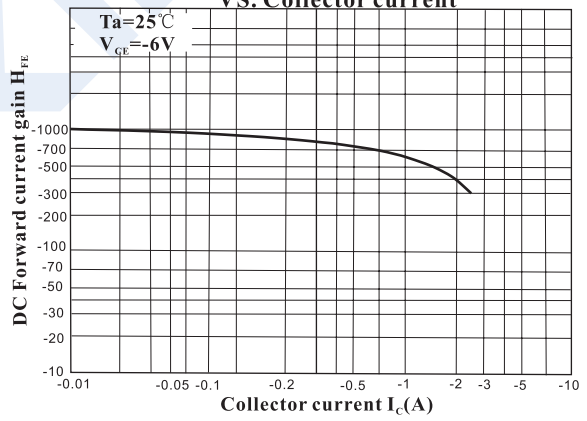
Common emitter output



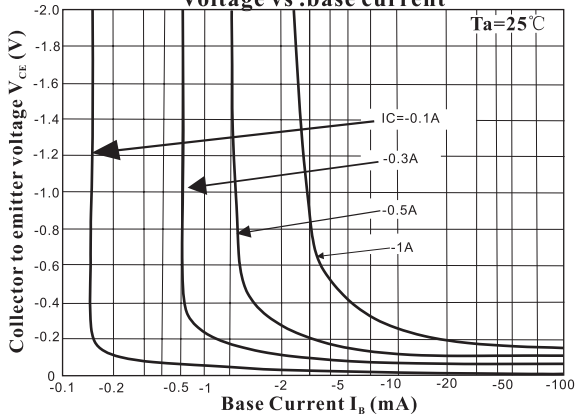
Common Emitter Transfer



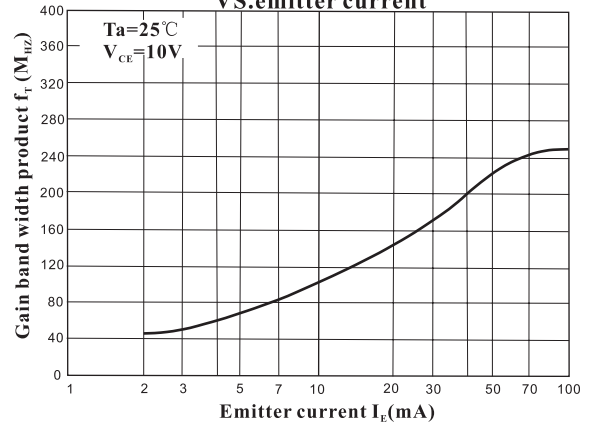
DC Forward current gain VS. Collector current



Collector to emitter saturation Voltage vs. base current



Gain band width product VS. emitter current



PNP Transistors

2SA1369

■ Typical Characteristics

